



b/a  
w/ all mngs.  
PATENT  
Attorney Docket No.: SAM-0219

Chenusa  
9/29/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Jae-Phil Boo, et al.

Examiner: Pham, L.

Serial No.: 09/902,243

Group Art Unit: 2823

Filing Date: July 10, 2001

Title: METHOD OF FABRICATING A NON-VOLATILE MEMORY DEVICE  
HAVING A TUNNEL-INSULATING LAYER INCLUDING MORE THAN  
TWO PORTIONS OF DIFFERENT THICKNESS

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

I hereby certify that this correspondence is being deposited with the United States Post Office as First Class Mail on the date indicated below in an envelope addressed to BOX NON-FEE AMENDMENT, Assistant Commissioner for Patents, Washington, DC 20231.

9-19-02

Date

Amy Green  
Amy Green

BOX NON-FEE AMENDMENT  
Assistant Commissioner for Patents  
Washington, D.C. 20231

AMENDMENT A

Sir:

This is in response to the Office Action mailed on June 19, 2002.

Please amend the application as follows:

In the Claims

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SEP 26 2002  
TECHNOLOGY CENTER 28800

*Subj A'*  
*/*  
1. (Amended) A method of fabricating a non-volatile memory device having a tunnel insulating layer, comprising:

sequentially depositing said tunnel insulating layer, a conductive layer, and a first insulating layer over a semiconductor substrate, said tunnel insulating layer including at least two portions of different thicknesses;

selectively etching the resultant structure to a given depth to form trenches;  
depositing a second insulating layer over said structure including said trenches;